ABSTRACT OF THE DISCLOSURE

PROCESS FOR PRODUCING SILICON WAFER

A process for producing a silicon wafer comprising a single-wafer etching step of performing an etching by supplying an etching solution through a supplying-nozzle to a surface of a single and a thin-discal wafer obtained by slicing a silicon single crystal ingot and rotating the wafer to spread the etching solution over all the surface of the wafer; and a grinding step of grinding the surface of the wafer, in this order, wherein the etching solution used in the single-wafer etching step is an aqueous acid solution which contains hydrogen fluoride, nitric acid, and phosphoric acid in an amount such that the content of which by weight % at a mixing rate of fluoric acid : nitric acid : phosphoric acid is 0.5 to 40% : 5 to 50% : 5 to 70%, respectively.

Figure 1